



GaAs pHEMT MMIC LOW NOISE AMPLIFIER, 6 - 26.5 GHz

Typical Applications

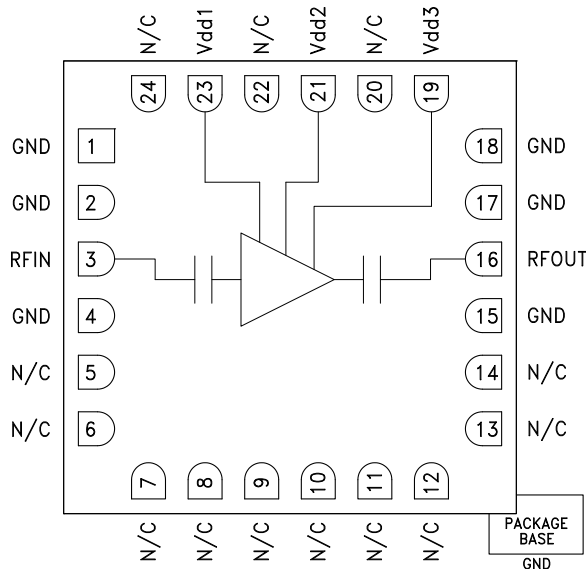
This HMC963LC4 is ideal for:

- Point-to-Point Radios
- Point-to-Multi-Point Radios
- Military & Space
- Test Instrumentation

Features

- Low Noise Figure: 2.5 dB
- High Gain: 22 dB
- P1dB Output Power: 10 dBm
- Single Supply Voltage: +3.5V @ 45mA
- Output IP3: +18 dBm
- 50 Ohm matched Input/Output
- 24 Lead 4x4 mm SMT Package: 16mm²

Functional Diagram



General Description

The HMC963LC4 is a self-biased GaAs MMIC Low Noise Amplifier housed in a leadless 4x4 mm ceramic surface mount package. The amplifier operates between 6 and 26.5 GHz, providing 20 dB of small signal gain, 2.5 dB noise figure, and output IP3 of +18 dBm, while requiring only 45 mA from a +3.5 V supply. The P1dB output power of +10 dBm enables the LNA to function as a LO driver for balanced, I/Q or image reject mixers. The HMC963LC4 also features I/Os that are DC blocked and internally matched to 50 Ohms, making it ideal for high capacity microwave radios and VSAT applications.

Electrical Specifications, $T_A = +25^\circ\text{C}$, $V_{dd1} = V_{dd2} = +3.5\text{V}$, $I_{dd} = 45\text{ mA}$

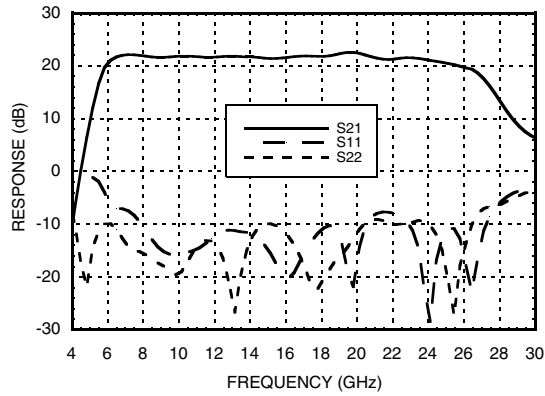
Parameter	Min.	Typ.	Max.	Units
Frequency Range	6 - 26.5			GHz
Gain	16.5	22		dB
Gain Variation over Temperature		0.03		dB / °C
Noise Figure [1]		2.5	3.5	dB
Input Return Loss		10		dB
Output Return Loss		10		dB
Output Power for 1 dB Compression	7	10		dBm
Saturated Output Power (P _{sat})		12		dBm
Output Third Order Intercept (IP3)		18		dBm
Supply Current (I _{dd}) (V _{dd} = 3.5V, V _{gg1} = V _{gg2} = Open)		45	70	mA

[1] Board loss subtracted out.

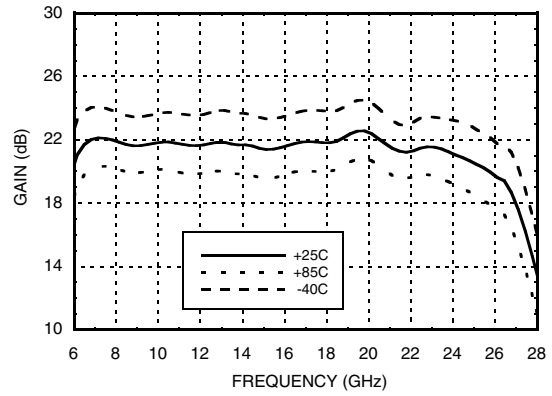


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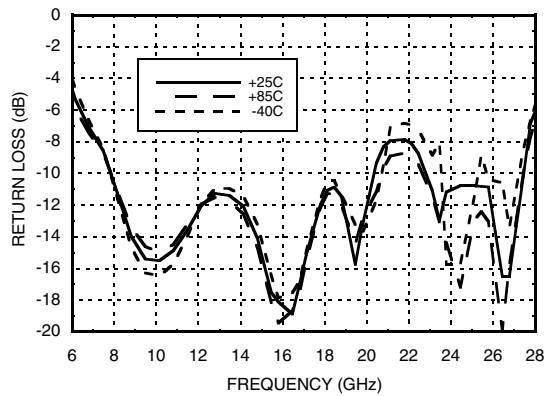
Broadband Gain & Return Loss



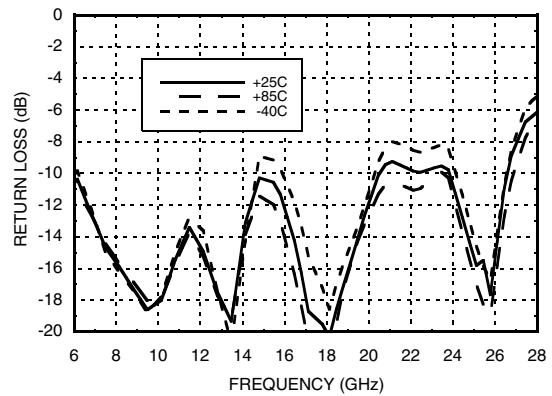
Gain vs. Temperature



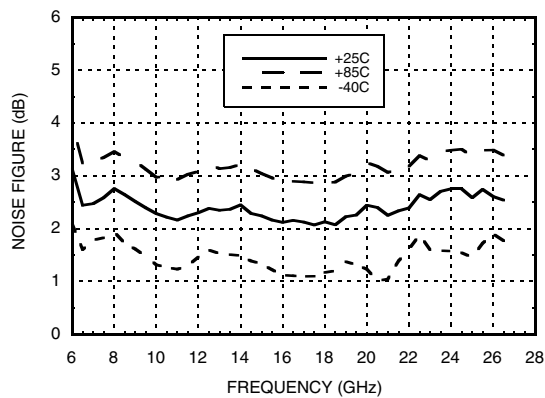
Input Return Loss vs. Temperature



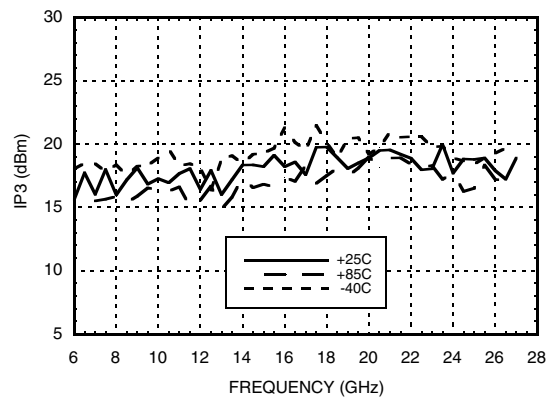
Output Return Loss vs. Temperature



Noise Figure vs. Temperature [1]



Output IP3 vs. Temperature

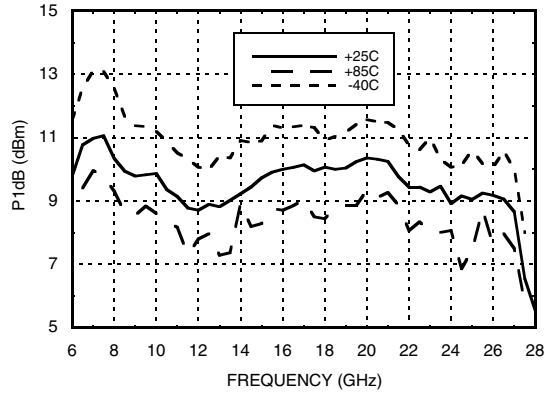


[1] Board loss subtracted out.

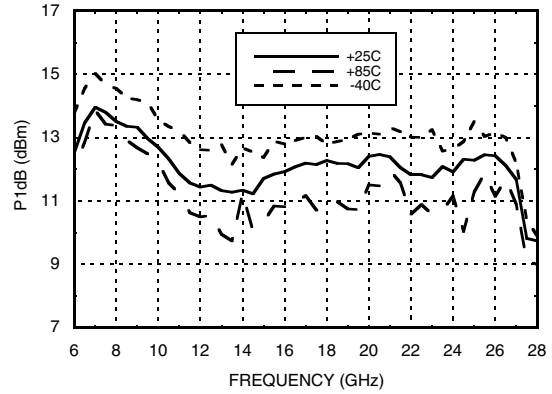


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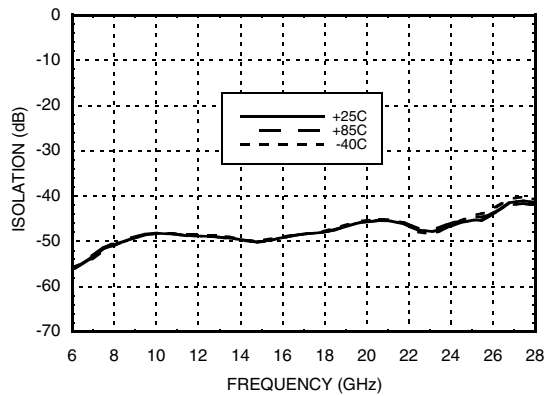
P1dB vs. Temperature



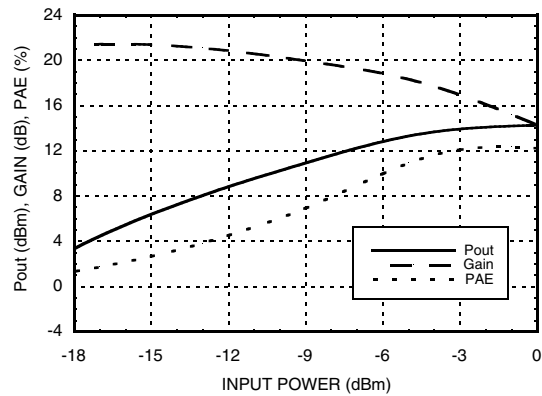
Psat vs. Temperature



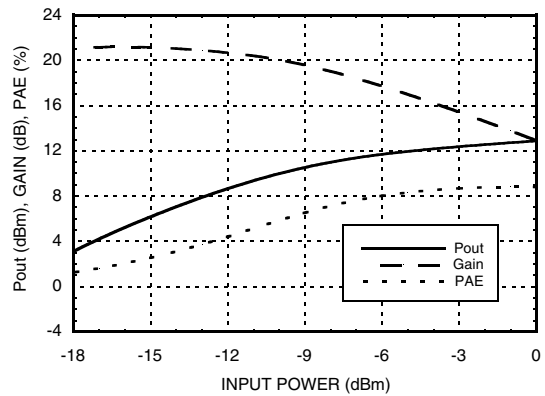
Reverse Isolation vs. Temperature



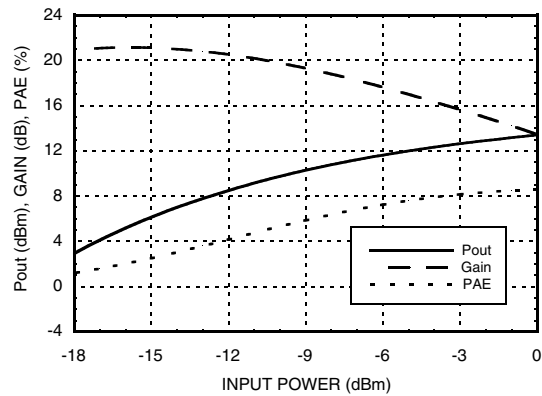
Power Compression @ 8 GHz



Power Compression @ 16 GHz



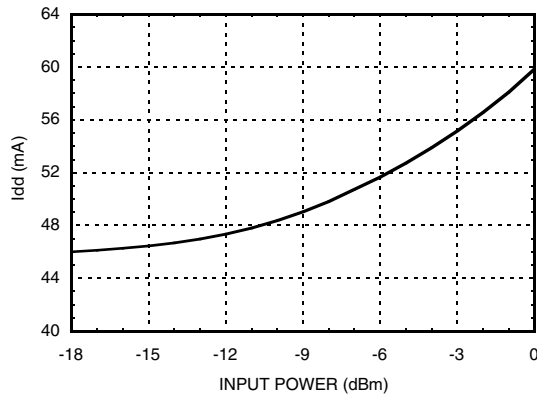
Power Compression @ 24 GHz





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Current vs. Input Power @ 16 GHz



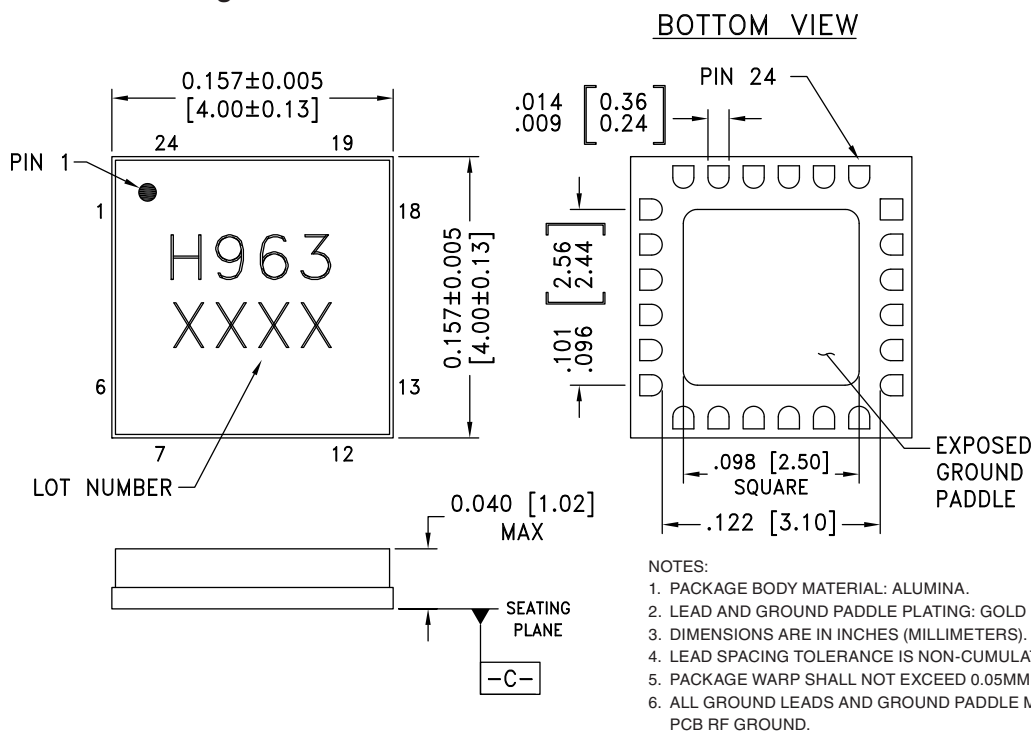
Absolute Maximum Ratings

Drain Bias Voltage	+4V
RF Input Power	0 dBm
Channel Temperature	150 °C
Continuous P _{diss} (T = 85 °C) (derate 8 mW/°C above 85 °C)	0.52 W
Thermal Resistance (Channel to ground paddle)	125 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C
ESD Sensitivity (HBM)	Class 0 <150 V



ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

Outline Drawing



Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking ^[2]
HMC963LC4	Alumina, White	Gold over Nickel	MSL3 ^[1]	H963 XXXX

[1] Max peak reflow temperature of 260 °C

[2] 4-Digit lot number XXXX

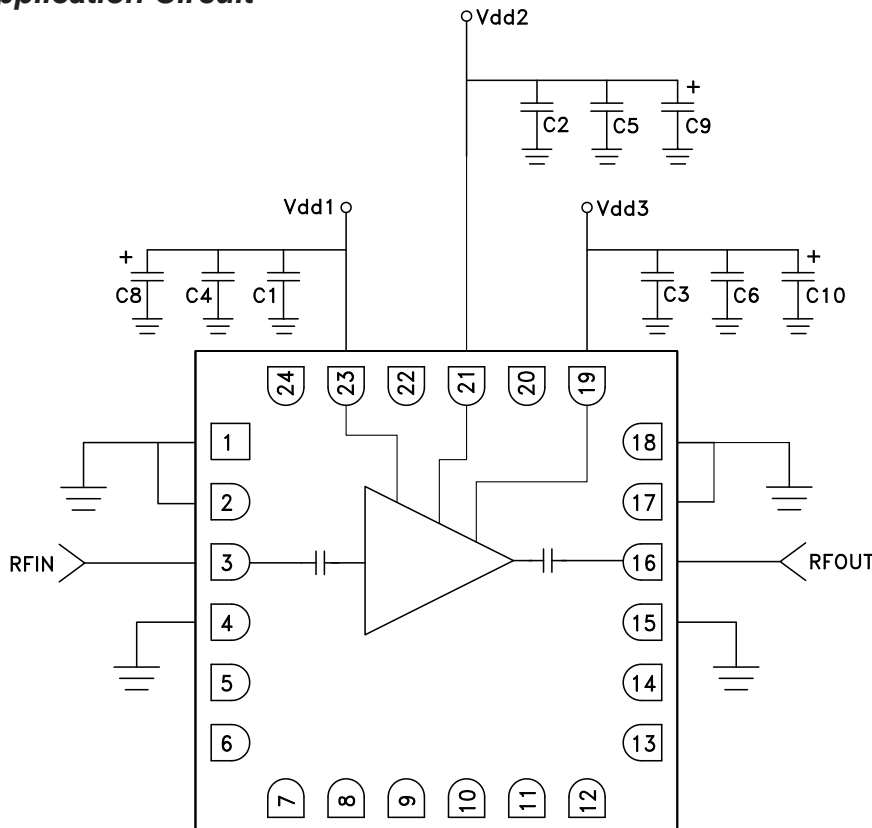


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Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 2, 4, 15, 17, 18	GND	These pins and package bottom must be connected to RF/DC ground.	
3	RFIN	This pin AC coupled and matched to 50 Ohms	
5 - 14, 20, 22, 24	N/C	No connection necessary. These pins may be connected to RF/DC ground. Performance will not be affected.	
16	RFOUT	This pin AC coupled and matched to 50 Ohms	
19, 21, 23	Vdd1, Vdd2, Vdd3	Power supply voltages for the amplifier. Bypass capacitors are required. See application circuit herein.	

Application Circuit



Capacitor	Value
C1 - C3	100 pF
C4 - C6	1000 pF
C8 - C10	2.2 μF